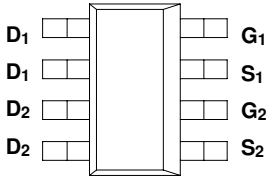


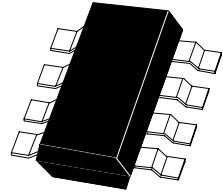
# SM-8 DUAL N-CANNEL ENHANCEMENT MODE AVALANCHE RATED MOSFET

ISSUE 1 - NOVEMBER 1995

## ZDM4206N



**PARTMARKING DETAIL – M4206N**



**SM-8  
(8 LEAD SOT223)**

### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	$V_{DS}$	60	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	$I_D$	1	A
Pulsed Drain Current	$I_{DM}$	8	A
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Body Diode Current at $T_{amb}=25^{\circ}C$	$I_{SD}$	1	A
Avalanche Current – Repetitive	$I_{AR}$	600	mA
Avalanche Energy – Repetitive	$E_{AR}$	15	mJ
Operating and Storage Temperature Range	$T_j-T_{stg}$	-55 to +150	$^{\circ}C$

### THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	VALUE	UNIT
Total Power Dissipation at $T_{amb} = 25^{\circ}C^*$ Any single die "on" Both die "on" equally	$P_{tot}$	2.25 2.75	W W
Derate above $25^{\circ}C^*$ Any single die "on" Both die "on" equally		18 22	mW/ $^{\circ}C$ mW/ $^{\circ}C$
Thermal Resistance - Junction to Ambient* Any single die "on" Both die "on" equally		55.6 45.5	$^{\circ}C/W$ $^{\circ}C/W$

\* The power which can be dissipated assuming the device is mounted in a typical manner on a PCB with copper equal to 2 inches square.

# ZDM 4206N

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

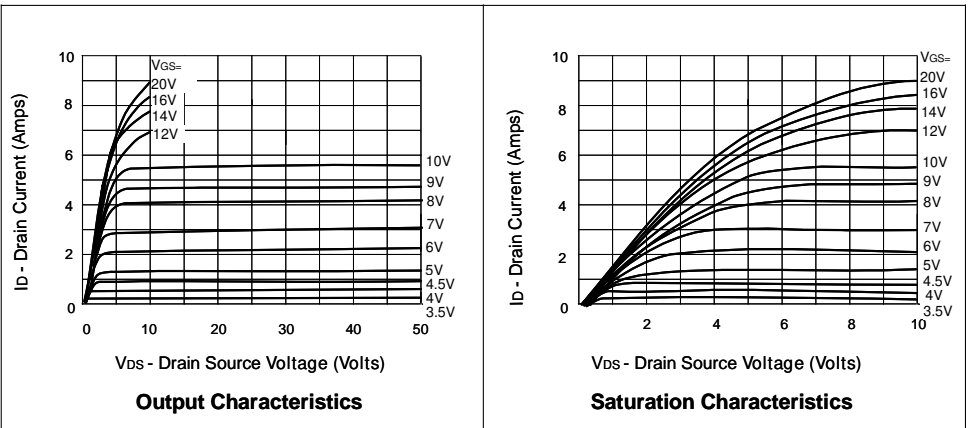
PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	$BV_{DSS}$	60		V	$I_D=1\text{mA}, V_{GS}=0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	1.3	3	V	$I_D=1\text{mA}, V_{DS}=V_{GS}$
Gate-Body Leakage	$I_{GSS}$		100	nA	$V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$
Zero Gate Voltage Drain Current	$I_{DSS}$		10 100	$\mu\text{A}$ $\mu\text{A}$	$V_{DS}=60\text{V}, V_{GS}=0$ $V_{DS}=48\text{V}, V_{GS}=0\text{V}, T=125^{\circ}\text{C}(2)$
On-State Drain Current(1)	$I_{D(on)}$	3		A	$V_{DS}=25\text{V}, V_{GS}=10\text{V}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		1 1.5	$\Omega$ $\Omega$	$V_{GS}=10\text{V}, I_D=1.5\text{A}$ $V_{GS}=5\text{V}, I_D=0.5\text{A}$
Forward Transconductance(1)(2)	$g_{fs}$	300		mS	$V_{DS}=25\text{V}, I_D=1.5\text{A}$
Input Capacitance (2)	$C_{iss}$		100	pF	$V_{DS}=25\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$
Common Source Output Capacitance (2)	$C_{oss}$		60	pF	
Reverse Transfer Capacitance (2)	$C_{rss}$		20	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		8	ns	$V_{DD}=25\text{V}, I_D=1.5\text{A}, V_{GEN}=10\text{V}$
Rise Time (2)(3)	$t_r$		12	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		12	ns	
Fall Time (2)(3)	$t_f$		15	ns	

(1) Measured under pulsed conditions. Width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$

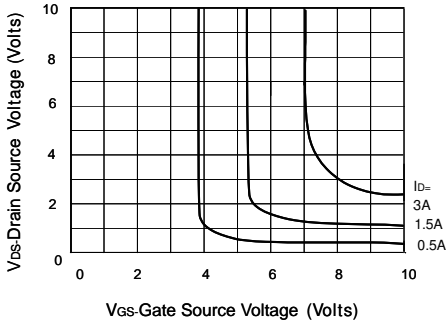
(2) Sample test.

(3) Switching times measured with 50 $\Omega$  source impedance and <5ns rise time on a pulse generator

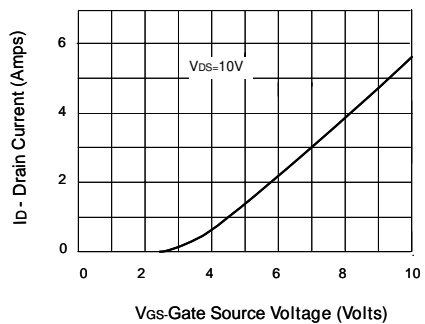
## TYPICAL CHARACTERISTICS



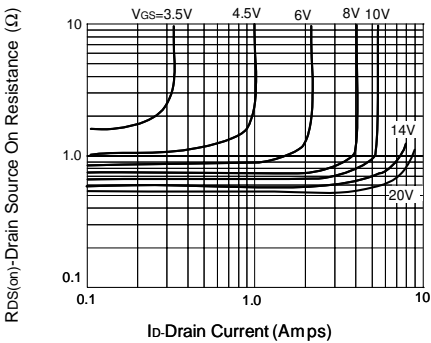
## TYPICAL CHARACTERISTICS



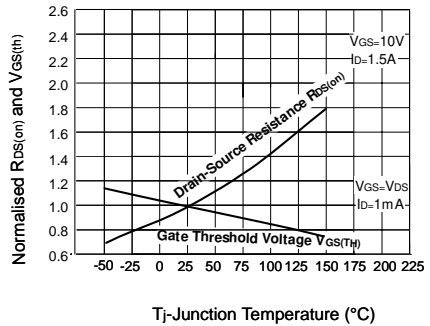
**Voltage Saturation Characteristics**



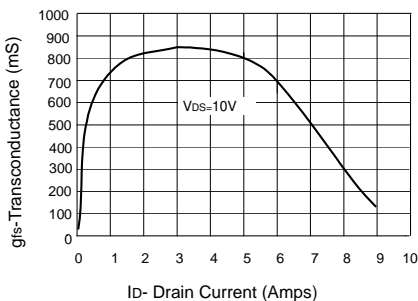
**Transfer Characteristics**



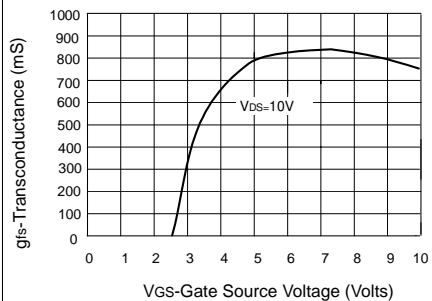
**On-resistance v drain current**



**Normalised  $R_{DS(on)}$  and  $V_{GS(th)}$  v Temperature**



**Transconductance v drain current**



**Transconductance v gate-source voltage**